

CLAIM AMENDMENTS

1.-8. (Cancelled)

9. (Previously Presented) An electrical device comprising:
electrical contact pads to receive a supply voltage;
a power bus electrically connected to the electrical contact pads; and
an interconnection circuit to, for each electrical contact pad, form a redundant connection between the bus and the electrical contact pad, wherein
the electrical device comprises a semiconductor device comprising multiple process layers, and
the interconnection circuit is formed in one of the process layers located between another one of the process layers in which the bus is formed and the electrical contact pads.

10.-11. (Cancelled)

12. (Original) The electrical device of claim 9, wherein the interconnection circuit comprises:
switches to selectively form the redundant connections.

13. (Original) The electrical device of claim 9, wherein the device comprises a microprocessor.

14.-19. (Cancelled)

20. (Currently Amended) A method usable with a semiconductor device, comprising:
electrical connecting external contacts of a semiconductor device to internal buses of the semiconductor device; ~~and~~
establishing redundant connections between the buses and the external contacts;
forming the buses in a first process layer; and
forming the redundant connections in a second process layer different from the first process layer.

21.-24. (Cancelled)

25. (New) The electrical device of claim 9, further comprising:
solder bumps electrically connected to the electrical contact pads.

26. (New) The electrical device of claim 9, wherein the interconnection circuit
comprises transistors to form the redundant connections.

27. (New) The method of claim 20, wherein the act of establishing redundant
connections comprises:
forming the redundant connections using transistors.

28. (New) The method of claim 20, wherein the act of establishing redundant
connections comprises:
establishing the redundant connections after fabrication of the semiconductor device.

29. (New) The method of claim 28, wherein the act of establishing the redundant
connections after fabrication of the semiconductor device comprises:
connecting the external contacts together based on a current density.